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FDG6316P

P-Channel 1.8V Specified PowerTrench® MOSFET

General Description

This P-Channel 1.8V specified MOSFET uses Fairchild's advanced low voltage PowerTrench process. It has been optimized for battery power management applications.

Applications

- · Battery management
- · Load switch

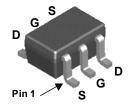
Features

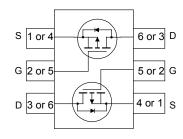
• -0.7 A, -12 V. $R_{DS(ON)}$ = 270 m Ω @ V_{GS} = -4.5 V $R_{DS(ON)}$ = 360 m Ω @ V_{GS} = -2.5 V

 $R_{DS(ON)}$ = 650 m Ω @ V_{GS} = -1.8 V

Low gate charge

- High performance trench technology for extremely low R_{DS(ON)}
- Compact industry standard SC70-6 surface mount package





SC70-6

The pinouts are symmetrical; pin 1 and pin 4 are interchangeable.

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-12	V
V _{GSS}	Gate-Source Voltage		± 8	V
I _D	Drain Current - Continuous	(Note 1)	-0.7	A
	– Pulsed		-1.8	
P _D	Power Dissipation for Single Operation (Note 1)		0.3	W
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

D	Thermal Resistance, Junction-to-Ambient	(Note 1)	415	°C/W
RθJA	I Thermal Resistance, Junction-to-Ambient	(Note 1)	413	- 6/00

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.16	FDG6316P	7"	8mm	3000 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics			•		
BV _{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{D} = -250 \mu\text{A}$	-12			V
<u>ΔBV_{DSS}</u> ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = –250 μ A, Referenced to 25°C		-3.7		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
I _{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = -8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			-100	nA
I _{GSSR}	Gate–Body Leakage, Reverse	$V_{GS} = 8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-0.4	-0.6	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = –250 μ A, Referenced to 25°C		2		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = -4.5 \text{ V}, I_D = -0.7 \text{ A}$ $V_{GS} = -2.5 \text{ V}, I_D = -0.5 \text{ A}$ $V_{GS} = -1.8 \text{ V}, I_D = -0.4 \text{ A}$ $V_{GS} = -4.5 \text{ V}, I_D = -0.7 \text{ A}, T_i = 125 ^{\circ}\text{C}$		221 297 427 250	270 360 650 348	mΩ
I _{D(on)}	On–State Drain Current	$V_{GS} = -4.5 \text{ V}, I_D = -0.7 \text{ A}, T_J = 125^{\circ}\text{C}$ $V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$	-1.8			Α
g _{FS}	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_{D} = -0.7 \text{ A}$		2.5		S
Dynamic	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = -6 \text{ V}, V_{GS} = 0 \text{ V},$		146		pF
Coss	Output Capacitance	f = 1.0 MHz		60		pF
C _{rss}	Reverse Transfer Capacitance			48		pF
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -6 \text{ V}, \qquad I_D = 1 \text{ A},$		5	10	ns
t _r	Turn-On Rise Time	V_{GS} = -4.5 V, R_{GEN} = 6 Ω		13	23	ns
t _{d(off)}	Turn-Off Delay Time			8	16	ns
t _f	Turn-Off Fall Time			2	4	ns
Qg	Total Gate Charge	$V_{DS} = -6 \text{ V}, I_{D} = -0.7 \text{ A},$		1.7	2.4	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -4.5 \text{ V}$		0.3		nC
Q_{gd}	Gate-Drain Charge			0.4		nC
Drain-So	ource Diode Characteristics	and Maximum Ratings	•			
I _s	Maximum Continuous Drain-Sour				-0.25	Α
V _{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \qquad I_S = -0.25 \text{ A}(\text{Note 2})$		-0.7	-1.2	V

Notes

^{1.} R_{0,IA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0,IC} is guaranteed by design while R_{0,IA} is determined by the user's board design. R_{0,IA} = 415°C/W when mounted on a minimum pad of FR-4 PCB on still air environment

^{2.} Pulse Test: Pulse Width < 300μ s, Duty Cycle < 2.0%

Typical Characteristics

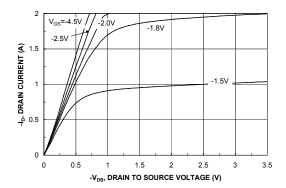


Figure 1. On-Region Characteristics.

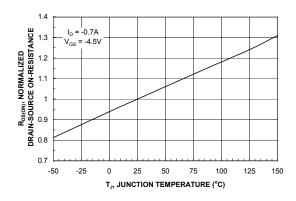


Figure 3. On-Resistance Variation with Temperature.

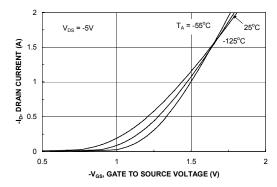


Figure 5. Transfer Characteristics.

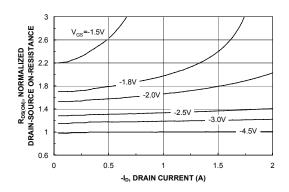


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

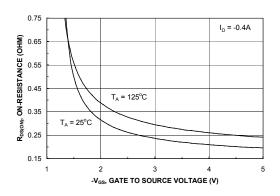


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

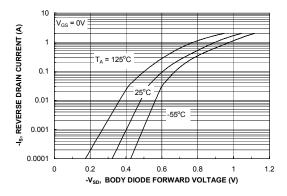
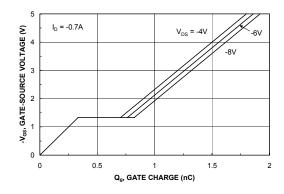


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



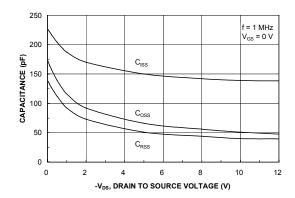
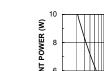
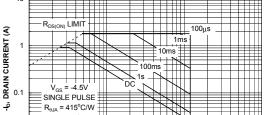


Figure 7. Gate Charge Characteristics.





T_A = 25°C

0.01

0.1

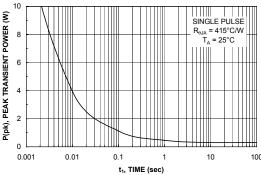


Figure 8. Capacitance Characteristics.

Figure 9. Maximum Safe Operating Area.

-V_{DS}, DRAIN-SOURCE VOLTAGE (V)

10



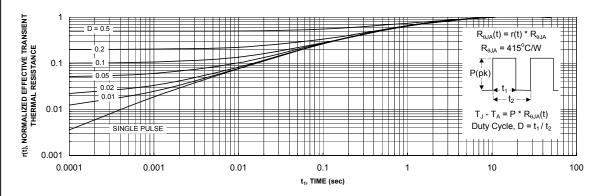


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1. Transient thermal response will change depending on the circuit board design.

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